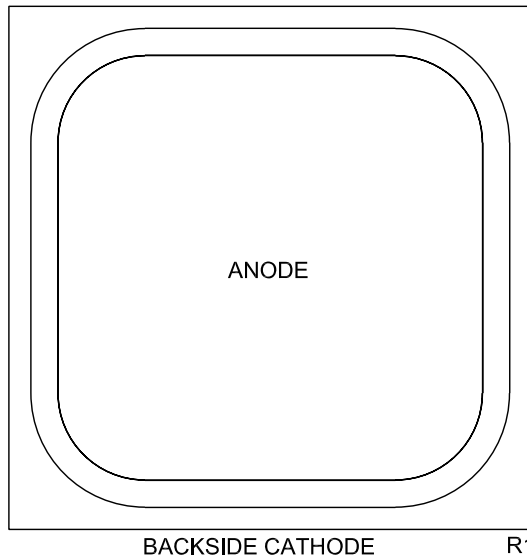


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	32 x 32 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	26 x 26 MILS
Top Side Metalization	Al - 20,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER

10,915

PRINCIPAL DEVICE TYPES

CMLSH1-40
1N5817
1N5818
1N5819

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